

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A photoelectric transducer comprising a first pin junction part including:
 - a first p-layer;
 - a first n-layer disposed so as to oppose the first p-layer; and
 - a first i-layer, disposed between the first p-layer and first n-layer, containing an iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom,wherein a composition ratio between the iron atom and the silicon atom in the first i-layer is in a range from 1:1.7 to ~~4:3.5~~1:3.5, and
wherein the first i-layer is formed by at least partly bonding the hydrogen atom to the silicon atom and the iron atom.
2. (Canceled)
3. (Previously Presented) A photoelectric transducer according to claim 1, wherein the first i-layer is mainly amorphous.
4. (Previously Presented) A photoelectric transducer according to claim 1, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.
5. (Previously Presented) A photoelectric transducer according to claim 1, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.
6. (Previously Presented) A photoelectric transducer according to claim 1, further comprising a second pin junction part, disposed in series with the first pin junction part, including:
 - a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and
a third i-layer disposed between the second p-layer and second n-layer and
made of an amorphous silicon film.

7. (Currently Amended) A photoelectric transducer apparatus comprising:
a substrate;
a first electrode layer disposed on one side of the substrate;
a second electrode layer disposed so as to oppose the first electrode layer; and
a first pin junction part including a first n-layer formed on the first electrode
layer, a first p-layer formed on one side of the second electrode layer so as to oppose the first
n-layer, and a first i-layer, disposed between the first p-layer and first n-layer, containing an
iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom,

wherein a composition ratio between the iron atom and the silicon atom in the
first i-layer is in a range from 1:1.7 to ~~4:3.5~~1:3.5, and

wherein the first i-layer is formed by at least partly bonding the hydrogen atom
to the silicon atom and the iron atom.

8. (Currently Amended) An iron silicide film for constructing an i-layer in a pin
junction;

the iron silicide film containing an iron atom, a silicon atom bonded to the iron
atom, and a hydrogen atom while being mainly amorphous,

wherein a composition ratio between the iron atom and the silicon atom is in a
range from 1:1.7 to ~~4:3.5~~1:3.5, and

wherein the first i-layer is formed by at least partly bonding the hydrogen atom
to the silicon atom and the iron atom.

9-10. (Canceled)

11. (Previously Presented) A photoelectric transducer according to claim 3, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.

12. (Canceled)

13. (Previously Presented) A photoelectric transducer according to claim 3, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

14. (Previously Presented) A photoelectric transducer according to claim 4, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

15. (Canceled)

16. (Previously Presented) A photoelectric transducer according to claim 3, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and made of an amorphous silicon film.

17. (Previously Presented) A photoelectric transducer according to claim 4, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and made of an amorphous silicon film.

18. (Previously Presented) A photoelectric transducer according to claim 1, wherein the composition ratio between the iron atom and silicon atom in the first i-layer is substantially 1:2.

19. (Previously Presented) A photoelectric transducer according to claim 7, wherein the composition ratio between the iron atom and silicon atom in the first i-layer is substantially 1:2.

20. (Previously Presented) An iron silicide film according to claim 8, wherein the composition ratio between the iron atom and silicon atom in the first i-layer is substantially 1:2.